

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1019-02** is Designed for VHF Communications up to 136 MHz

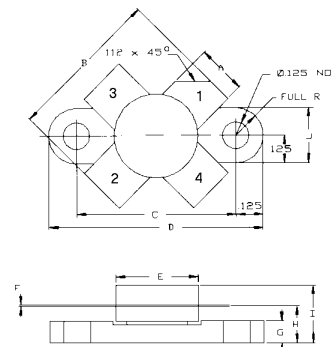
FEATURES:

- $P_G = 4.5$ dB Minimum at 150 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	117 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.7°C/W

PACKAGE STYLE .380 4 LEAD FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.250/.5,35	.250/.634
B	.785/.78,94	
C	.778/.78,29	.738/.78,54
D	.970/.94,64	.980/.94,89
E		.385/.78,78
F	.004/.0,10	.006/.0,15
G	.095/.0,16	.105/.0,26,7
H	.160/.4,35	.188/.4,57
I		.238/.7,11
J	.242/.6,11	.255/.6,40

1 = COLLECTOR 3 & 4 = EMITTER 2 = BASE

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V		1.5		mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0			---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz			150	pF
P_{OUT} P_G	$V_{CC} = 13.5$ V $P_{IN} = 10.6$ W $f = 150$ MHz	30 4.5			W dB